TPMEG6030ELP-QX

Surface mount LVF Schottky diode

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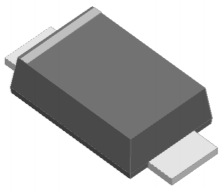
Features

LVF Schottky chip
Low VF， Low power losses, high efficiency
Ldeal for surface mounted applications
Plastic Case Material has UL Flammability

Mechanical Data

Package: SMAF
Terminals:Tin Plated leads, solderable per Mil-STD-750 Method 2026
Polarity: As marked
Molding compound meets UL 94 V-0 flammability rating, ROHS-compliant



SMAF

Maximum Ratings (Ta=25℃ Unless otherwise specified)

Type Number	SYMBOL	TPMEG6030ELP-QX	Umit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	60	V
Maximum RMS Voltage	V_{RMS}	42	V
Maximum DC Blocking Voltage	V_{DC}	60	V
Maximum Average Forward Rectified Current	$IO_{(AV)}$	3.0	A
Peak Forward Surge Current 8.3ms Single half-sine-wave superimposed on rated load(JEDEC Method) on rated	IFSM	60.0	A
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25℃		120.0	A
Current squared time @1ms≤t8.3≤ms Tj=25℃， Rating of per diode	I^2t	14.9	A^2S
Maximum Forward Voltage at 3.0A DC	V_{FM}	0.55	V
Maximum Reverse Current TA = 25℃	IR	0.2	mA
at Rated DC Blocking Voltage TA = 80℃		50	mA
Typical Thermal Resistance	R_{QJA}	65.0	℃/W
Operating Junction Temperature Range	T_J	—55to+150	℃
Storage Temperature Range	T_{STG}	—55to+150	℃

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FIG. 1MAXIMUM AVERAGE FORWARD CURRENT DERATING

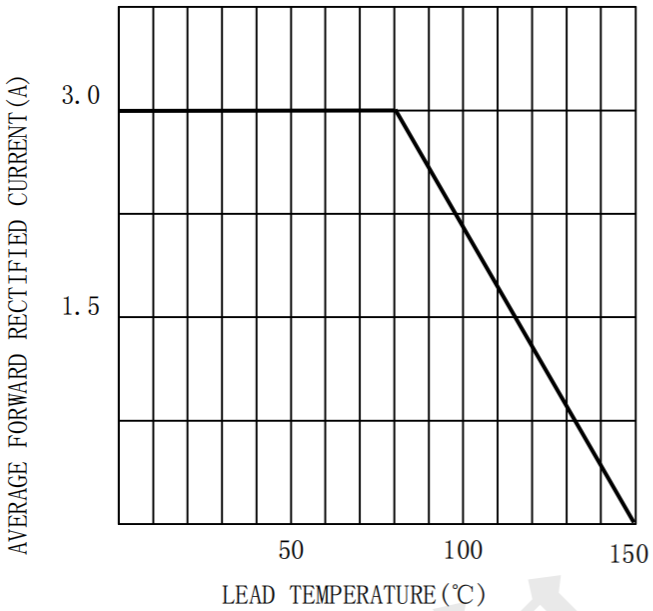


FIG. 2TYPICAL FORWARD CHARACTERISTICS

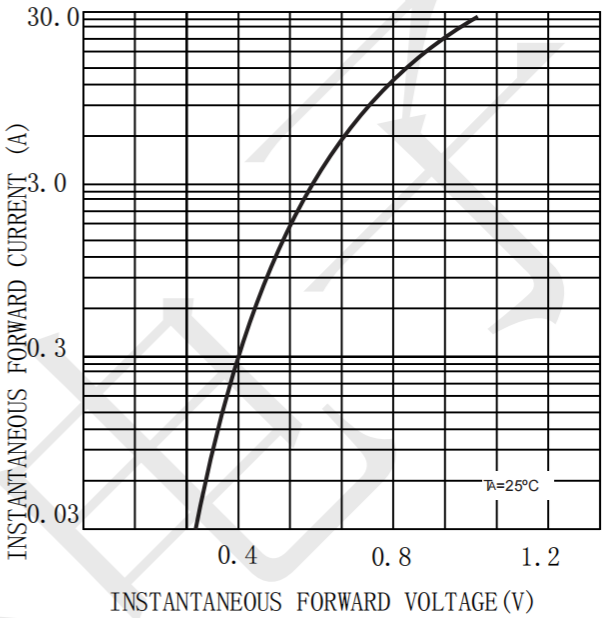


FIG. 3MAXIMUM NON-REPEITIVE SURGE CURRENT

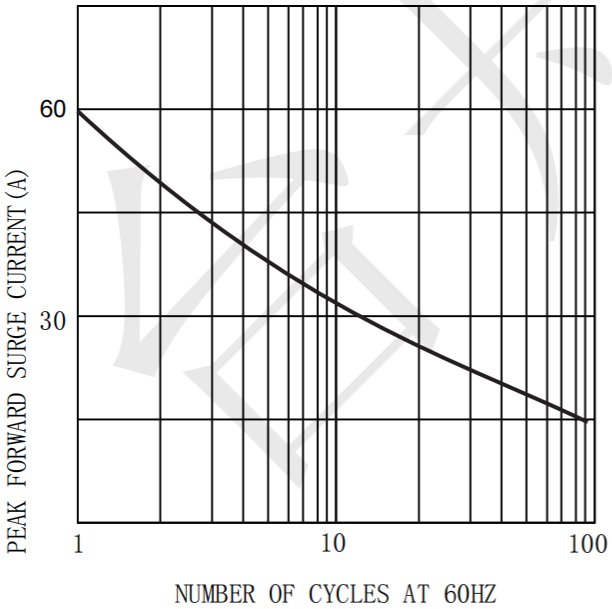
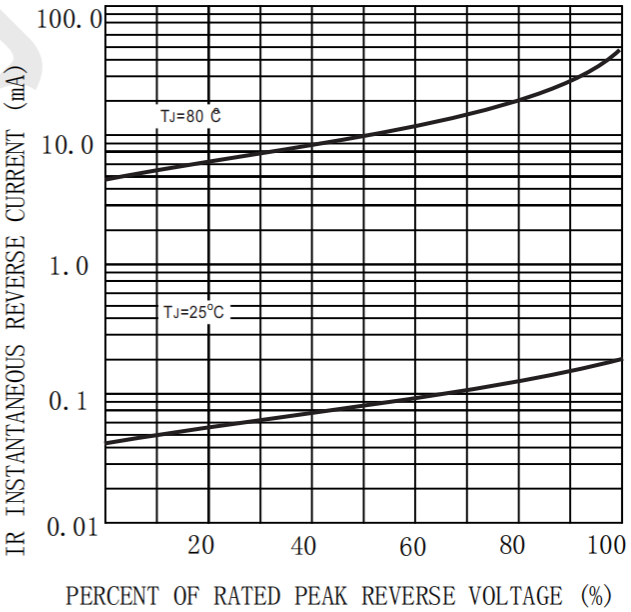
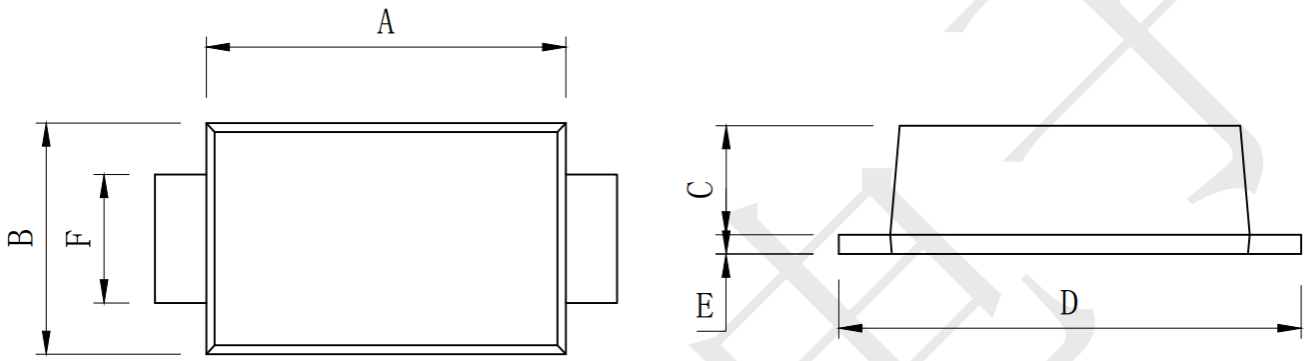


FIG. 4 TYPICAL REVERSE CHARACTERISTICS(per element)



Outline Dimensions

SMAF



SMAF				
DIM	INC HES		MM	
	MIN	MAX	MIN	MAX
A	0.13	0.15	3.2	3.8
B	0.09	0.11	2.3	2.7
C	0.03	0.05	0.8	1.2
D	0.16	0.20	4	5
E	/	0.01	/	0.3
F	0.04	0.08	1	2